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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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Application Number	10/721920
Filing Date	November 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2822
Examiner Name	Trinh, Michael

Sheet 1 of 4

Attorney Docket No: 303.685US2

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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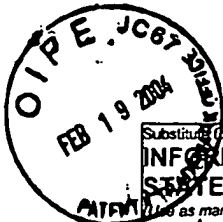
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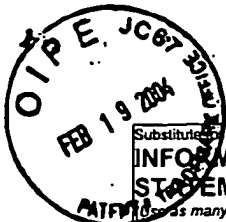
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	Application Number	10/721920
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	First Named Inventor	Ahn, Kie
	Group Art Unit	2822
	Examiner Name	Trinh, Michael
Sheet 3 of 4	Attorney Docket No: 303.685US2	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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Sheet 4 of 4

Attorney Docket No: 303.685US2

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DATE CONSIDERED

12/12/04

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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional): Applicant is to place a check mark here if English language Translation is attached

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Applicant Number	Unknown 10/721920
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown 2822
Examiner Name	Unknown

Sheet 1 of 9

Attorney Docket No: 303.685US2

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Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 303.685US2

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Application Number	Unknown 10/721920
Filing Date	Even Date Herewith
First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
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	First Named Inventor	Ahn, Kie
	Group Art Unit	Unknown
	Examiner Name	Unknown
Sheet 6 of 9	Attorney Docket No: 303.685US2	

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	Group Art Unit	Unknown
	Examiner Name	Unknown
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Applicant Number	Unknown 10/721920
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First Named Inventor	Ahn, Kie
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 8 of 9

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	Group Art Unit	Unknown
	Examiner Name	Unknown
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PT		WOLF, S. , "Chapter 4: Multilevel-Interconnect Technology for VLSI and ULSI", In: Silicon Processing for the VLSI Era, Vol. 2 Process Integration, Lattice Press, Sunset Beach, CA, (1990), 176-297	

EXAMINER	Michael Trib.	DATE CONSIDERED	12/12/04
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